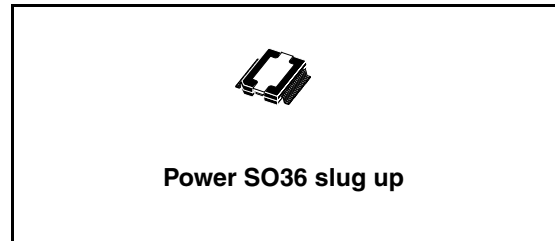


60 V 6 A quad power half bridge**Features**

- Minimum input output pulse width distortion
- 200 m Ω R_{dsON} complementary DMOS output stage
- CMOS compatible logic inputs
- Thermal protection
- Thermal warning output
- Under voltage protection

**Description**

STA517B is a monolithic quad half bridge stage in Multipower BCD Technology. The device can be used as dual bridge or reconfigured, by connecting CONFIG pin to V_{dd} pin, as single bridge with double current capability, and as half bridge (Binary mode) with half current capability.

The device is particularly designed to make the output stage of a stereo all-digital high efficiency (DDX™) amplifier capable to deliver 175 + 175 W @ THD = 10 % at V_{cc} 54 V output power on 8 Ω load and 350 W @ THD = 10 % at V_{cc} 54 V on 4 Ω load in single BTL configuration.

The input pins have threshold proportional to V_L pin voltage.

Table 1. Device summary

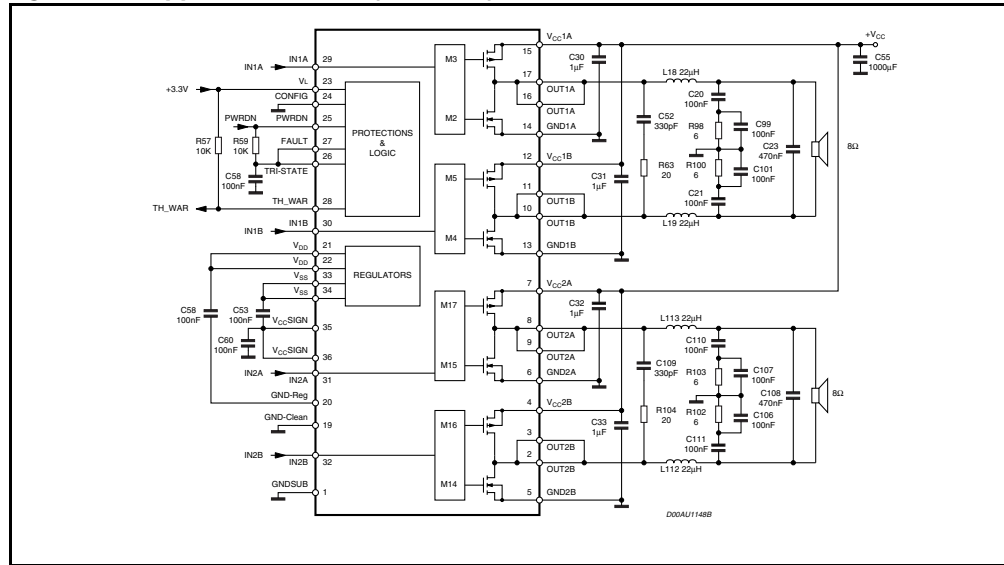
| Part number | Package | Packaging |
|-------------|--------------------|---------------|
| STA517B | Power SO36 slug up | Tube |
| STA517B13TR | Power SO36 slug up | Tape and reel |

Contents

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1 Introduction

Figure 1. Application circuit (dual BTL)



2 Pin lists

Table 2. Pin function

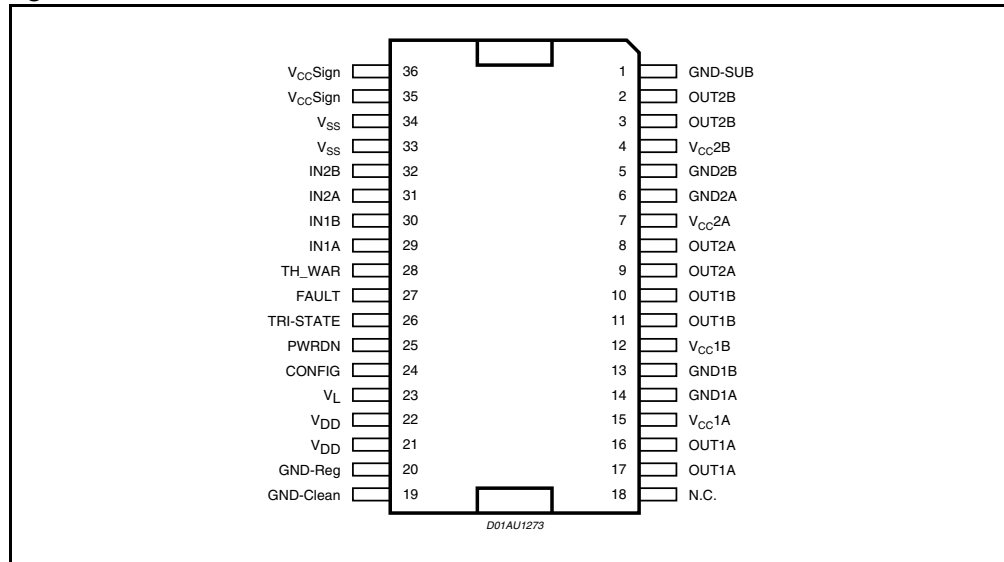
| Number | Pin | Description |
|--------|----------------|--|
| 1 | GND-SUB | Substrate ground |
| 2, 3 | OUT2B | Output half bridge 2B |
| 4 | VCC2B | Positive supply |
| 5 | GND2B | Negative supply |
| 6 | GND2A | Negative supply |
| 7 | VCC2A | Positive supply |
| 8, 9 | OUT2A | Output half bridge 2A |
| 10, 11 | OUT1B | Output half bridge 1B |
| 12 | VCC1B | Positive supply |
| 13 | GND1B | Negative supply |
| 14 | GND1A | Negative supply |
| 15 | VCC1A | Positive supply |
| 16, 17 | OUT1A | Output half bridge 1A |
| 18 | NC | Not connected |
| 19 | GND-CLEAN | Logical ground |
| 20 | GND-REG | Ground for regulator V _{dd} |
| 21, 22 | VDD | 5 V regulator referred to ground |
| 23 | V _L | High logical state setting voltage |
| 24 | CONFIG | Configuration pin |
| 25 | PWRDN | Stand-by pin |
| 26 | TRI-STATE | Hi-Z pin |
| 27 | FAULT | Fault pin advisor |
| 28 | TH-WAR | Thermal warning advisor |
| 29 | IN1A | Input of half bridge 1A |
| 30 | IN1B | Input of half bridge 1B |
| 31 | IN2A | Input of half bridge 2A |
| 32 | IN2B | Input of half bridge 2B |
| 33, 34 | VSS | 5 V regulator referred to +V _{cc} |
| 35, 36 | VCC SIGN | Signal positive supply |

Table 3. Functional pin status

| Pin name | Logical value | Status |
|-----------------------|---------------|---|
| FAULT | 0 | Fault detected (short circuit or thermal for example) |
| FAULT ⁽¹⁾ | 1 | Normal operation |
| TRI-STATE | 0 | All powers in Hi-Z state |
| TRI-STATE | 1 | Normal operation |
| PWRDN | 0 | Low absorption |
| PWRDN | 1 | Normal operation |
| THWAR | 0 | Temperature of the IC =130 °C |
| THWAR ⁽¹⁾ | 1 | Normal operation |
| CONFIG | 0 | Normal operation |
| CONFIG ⁽²⁾ | 1 | OUT1A=OUT1B; OUT2A=OUT2B (IF IN1A = IN1B; IN2A = IN2B) |

1. The pin is open collector. To have the high logic value, it needs to be pulled up by a resistor.
2. CONFIG = 1 means connect Pin 24 (CONFIG) to Pins 21, 22 (Vdd)

Figure 2. Pin connection



3 Electrical characteristics

Table 4. Absolute maximum ratings

| Symbol | Parameter | Value | Unit |
|----------------|------------------------------------|------------|------|
| V_{CC} | DC supply voltage (Pins 4,7,12,15) | 60 | V |
| V_{max} | Maximum voltage on pins 23 to 32 | 5.5 | V |
| T_{op} | Operating temperature range | 0 to 70 | °C |
| T_{stg}, T_j | Storage and junction temperature | -40 to 150 | °C |

Table 5. Thermal data

| Symbol | Parameter | Min. | Typ. | Max. | Unit |
|--------------|---|------|------|------|------|
| T_{j-case} | Thermal resistance junction to case (thermal pad) | | 1 | 2.5 | °C/W |
| T_{jSD} | Thermal shut-down junction temperature | | 150 | | °C |
| T_{warn} | Thermal warning temperature | | 130 | | °C |
| t_{hSD} | Thermal shut-down hysteresis | | 25 | | °C |

Table 6. Electrical characteristics
($V_L = 3.3$ V; $V_{CC} = 50$ V; $T_{amb} = 25$ °C unless otherwise specified)

| Symbol | Parameter | Test conditions | Min. | Typ. | Max. | Unit |
|---------------|--|--|-----------------|------|-----------------|------|
| R_{dsON} | Power Pchannel/Nchannel MOSFET R_{dsON} | $I_d=1A$ | | 200 | 240 | mΩ |
| I_{dss} | Power Pchannel/Nchannel leakage I_{dss} | | | | 100 | μA |
| g_N | Power Pchannel R_{dsON} matching | $I_d=1A$ | 95 | | | % |
| g_P | Power Nchannel R_{dsON} matching | $I_d=1A$ | 95 | | | % |
| Dt_s | Low current dead time (static) | see Figure 4 | | 10 | 20 | ns |
| Dt_d | High current dead time (dynamic) | $L=22\mu H, C = 470nF$ $R_l = 8 \Omega, I_d=4.5A$ see Figure 5 | | | 50 | ns |
| t_{dON} | Turn-on delay time | Resistive load | | | 100 | ns |
| t_{dOFF} | Turn-off delay time | Resistive load | | | 100 | ns |
| t_r | Rise time | Resistive load see Figure 4 | | | 25 | ns |
| t_f | Fall time | Resistive load see Figure 4 | | | 25 | ns |
| V_{CC} | Supply operating voltage | | 10 | | 56 | V |
| $V_{IN-High}$ | High level input voltage | | | | $V_L/2 + 300mV$ | V |
| V_{IN-Low} | Low level input voltage | | $V_L/2 - 300mV$ | | | V |
| I_{IN-H} | High level Input current | Pin voltage = V_L | | 1 | | μA |
| I_{IN-L} | Low level input current | Pin voltage = 0.3 V | | 1 | | μA |

Table 6. Electrical characteristics (continued)
($V_L = 3.3\text{ V}$; $V_{CC} = 50\text{ V}$; $T_{amb} = 25\text{ °C}$ unless otherwise specified)

| Symbol | Parameter | Test conditions | Min. | Typ. | Max. | Unit |
|-----------------|---|--|------|------|------|---------------|
| $I_{PWRDN-H}$ | High level PWRDN pin input current | $V_L = 3.3\text{ V}$ | | 35 | | μA |
| V_{Low} | Low logical state voltage V_L (pin PWRDN, TRISTATE)(see Table 7) | $V_L = 3.3\text{ V}$ | 0.8 | | | V |
| V_{High} | High logical state voltage V_H (pin PWRDN, TRISTATE)(see Table 7) | $V_L = 3.3\text{ V}$ | | | 1.7 | V |
| $I_{VCC-PWRDN}$ | Supply current from V_{CC} in power down | $PWRDN = 0$ | | | 3 | mA |
| I_{FAULT} | Output current pins FAULT -TH-WARN when FAULT CONDITIONS | $V_{pin} = 3.3\text{ V}$ | | 1 | | mA |
| $I_{VCC-hiz}$ | Supply current from V_{CC} in Tristate | Tristate = 0 | | 22 | | mA |
| I_{VCC} | Supply current from V_{CC} in operation both channel switching) | Input pulse width = 50 % duty Switching frequency = 384 KHz; No LC filters | | 70 | | mA |
| I_{OUT-SH} | Over current protection threshold I_{sc} (short circuit current limit) ¹ | | 6.5 | 8 | 10 | A |
| V_{UV} | Under voltage protection threshold | | | 7 | | V |
| V_{OV} | Over voltage protection threshold | | 60 | | 70 | V |
| t_{pw_min} | Output minimum pulse width | No load | 25 | | 40 | ns |

1. See specific application note number: AN1994.

Table 7. V_{Low} , V_{High} variation with V_L

| V_L | $V_{Low\ min}$ | $V_{High\ max}$ | Unit |
|-------|----------------|-----------------|------|
| 2.7 | 0.7 | 1.5 | V |
| 3.3 | 0.8 | 1.7 | V |
| 5 | 0.85 | 1.85 | V |

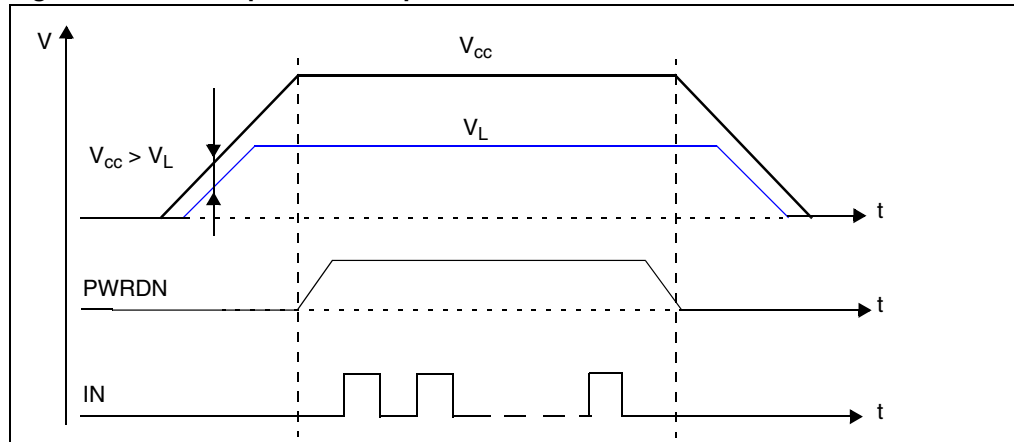
Table 8. Logic truth table (see [Figure 2](#))

| Tristate | INxA | INxB | Q1 | Q2 | Q3 | Q4 | Output mode |
|----------|------|------|-----|-----|-----|-----|-------------|
| 0 | x | x | OFF | OFF | OFF | OFF | Hi-Z |
| 1 | 0 | 0 | OFF | OFF | ON | ON | DUMP |
| 1 | 0 | 1 | OFF | ON | ON | OFF | NEGATIVE |
| 1 | 1 | 0 | ON | OFF | OFF | ON | POSITIVE |
| 1 | 1 | 1 | ON | ON | OFF | OFF | Not used |

4 Power supply and control sequencing

To guarantee correct operation and reliability, a correct turn on/off sequence must be followed. [Figure 3](#) shows the correct power on sequence.

Figure 3. Correct power-on sequence



V_{CC} must turn on before V_L in order to prevent uncontrolled current flowing through an internal protection diode connected between V_L (logic supply) and V_{CC} (high power supply). Failure to do so could result in damage to the device.

PWRDN must be released after V_L is switched on. An input signal can then be sent to the power stage.

5 Test

Figure 4. Test circuit

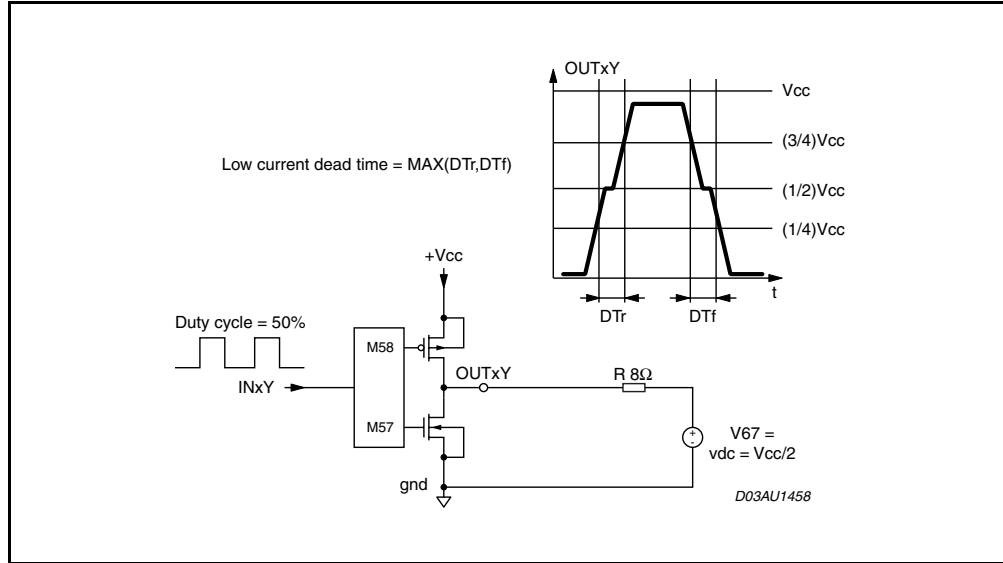


Figure 5. Current dead time test circuit

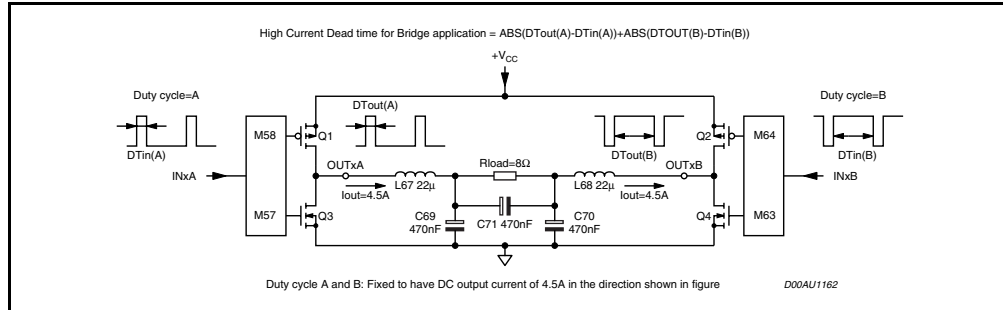


Figure 6. Typical single BTL configuration to obtain 350 W @ THD 10 %, RL = 4 Ω, VCC = 54 V (a)

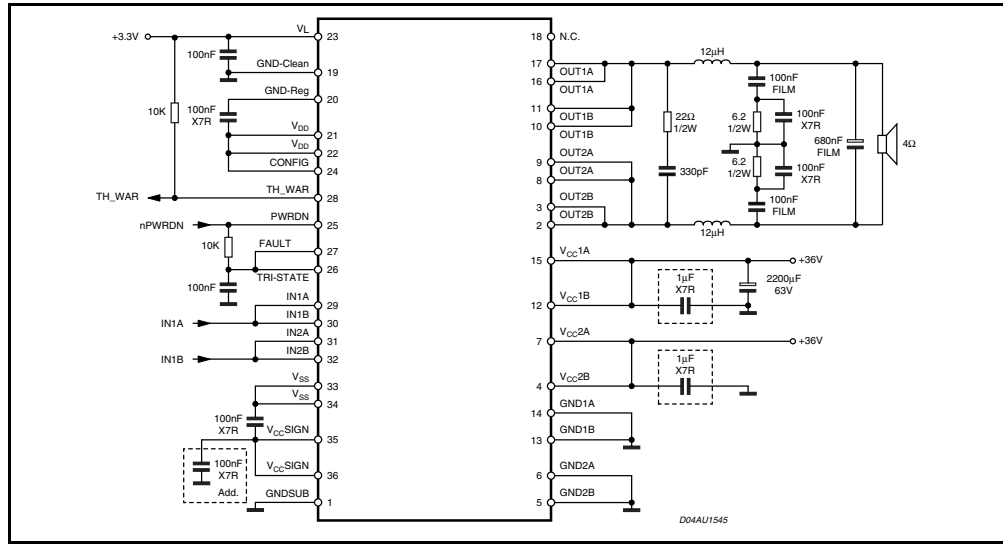
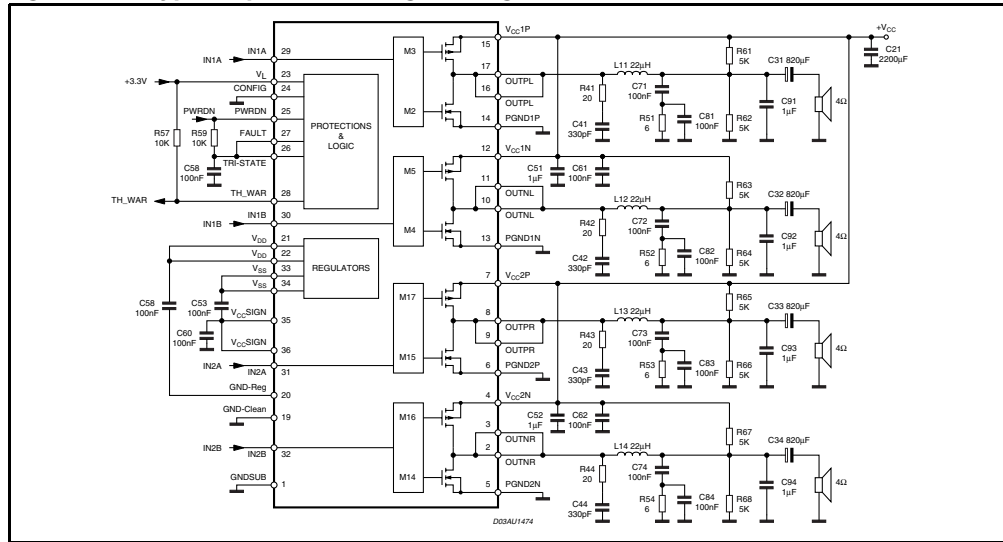


Figure 7. Typical quad half bridge configuration

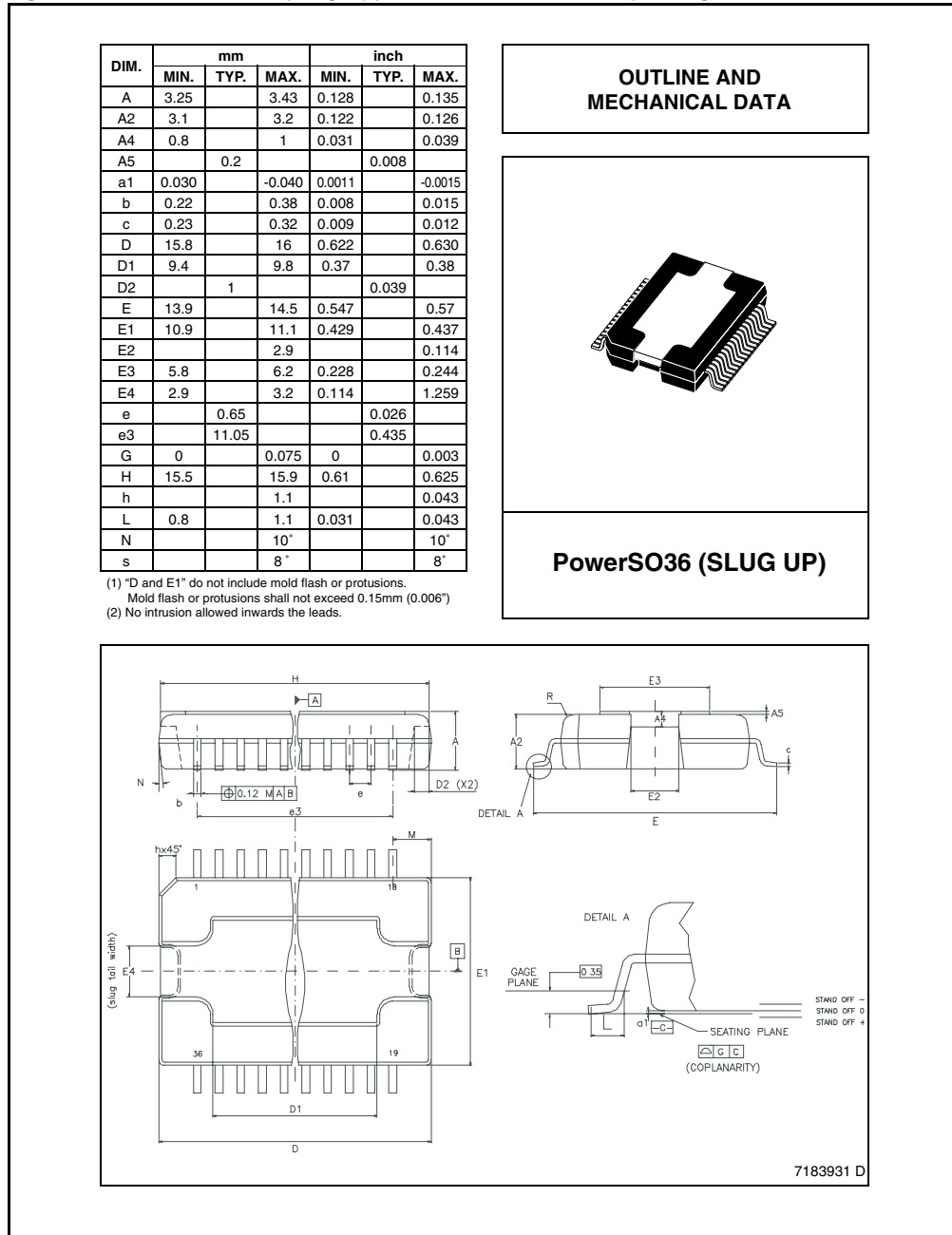


For more information, refer to the application note “ST50X and STA51X digital power amplifiers”.

a. A PWM modulator as driver is required. This result was obtained using the STA30X+STA50X demo board.

6 Mechanical and package data

Figure 8. Power SO36 (slug up) mechanical data and package dimension



7 Revision history

Table 9. Document revision history

| Date | Revision | Changes |
|-------------|----------|-------------------------------------|
| 01-Feb-2007 | 1 | Initial release |
| 19-Mar-2007 | 2 | Update to reflect product maturity. |

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